	TED STATES PATENT	and Trademark Office	UNITED STATES DEPART United States Patent and T Address: COMMISSIONER OF P Washington, D.C. 2023: www.uspto.gov	rademark Office ATENTS AND TRADEMARKS
APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/907,373	07/17/2001	Akira Mizumura	09792909-5096	6501
SONNENSC	7590 06/14/2002 CHEIN NATH & ROS	EXAMINER		
P.O. BOX 061080 WACKER DRIVE STATION CHICAGO, IL 60606-1080			NGUYEN, KHIEM D	
CHICAGO, II	2 00000-1080		ART UNIT	PAPER NUMBER
		_	2823 DATE MAILED: 06/14/2002	

Please find below and/or attached an Office communication concerning this application or proceeding.

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		Application No.	Applicant(s)		
	•	09/907,373	MIZUMURA, AKIRA		
Office Action Summary		Examiner	Art Unit		
		Khiem D Nguyen	2823		
	- The MAILING DATE of this communication ap	pears on the cover sheet	with the correspondence address		
Period fo					
THE N - Extense - If the p - If NO - Failure - Any re	DRTENED STATUTORY PERIOD FOR REPL MAILING DATE OF THIS COMMUNICATION. sions of time may be available under the provisions of 37 CFR 1. SIX (6) MONTHS from the mailing date of this communication. period for reply specified above is less than thirty (30) days, a rep period for reply is specified above, the maximum statutory period to reply within the set or extended period for reply will, by statute ply received by the Office later than three months after the mailing d patent term adjustment. See 37 CFR 1.704(b).	136(a). In no event, however, may ly within the statutory minimum of t will apply and will expire SIX (6) M4 e, cause the application to become	a reply be timely filed hirty (30) days will be considered timely. ONTHS from the mailing date of this communication, ABANDONED (35 U.S.C. § 133).		
Status					
1)	Responsive to communication(s) filed on	<u> </u>			
2a)	This action is FINAL . 2b) T	his action is non-final.			
3)∏ Dispositio	Since this application is in condition for allow closed in accordance with the practice under on of Claims				
4)⊠	Claim(s) <u>1 and 2</u> is/are pending in the applica	ation.			
4	4a) Of the above claim(s) is/are withdra	wn from consideration.			
5)	Claim(s) is/are allowed.				
6)🛛	Claim(s) <u>1-2</u> is/are rejected.				
7)	Claim(s) is/are objected to.				
	Claim(s) are subject to restriction and/o on Papers	or election requirement.			
9) 🗌 T	The specification is objected to by the Examine	er.			
10)🛛 T	he drawing(s) filed on <u>17 July 2001</u> is/are: a)	🛛 accepted or b) 🗌 objecte	ed to by the Examiner.		
	Applicant may not request that any objection to the	ne drawing(s) be held in abe	eyance, See 37 CFR 1,85(a).		
11) 🗌 T	he proposed drawing correction filed on	_ is: a)□ approved b)□	disapproved by the Examiner.		
	If approved, corrected drawings are required in re	eply to this Office action.			
12)[] T	he oath or declaration is objected to by the E	xaminer.			
Priority u	nder 35 U.S.C. §§ 119 and 120				
13)🕅	Acknowledgment is made of a claim for foreig	n priority under 35 U.S.C	C. § 119(a)-(d) or (f).		
a)[2	All b) Some * c) None of:				
	1. Certified copies of the priority documen	ts have been received.			
	2. Certified copies of the priority documents have been received in Application No				
	3. Copies of the certified copies of the price application from the International Be ee the attached detailed Office action for a list	ureau (PCT Rule 17.2(a))).		
14) 🗋 A	cknowledgment is made of a claim for domest	tic priority under 35 U.S.C	C. § 119(e) (to a provisional application)		
	☐ The translation of the foreign language pr cknowledgment is made of a claim for domes				
Attachment	(s)				
2) 🗌 Notice	e of References Cited (PTO-892) e of Draftsperson's Patent Drawing Review (PTO-948) pation Disclosure Statement(s) (PTO-1449) Paper No(s) _	5) 📃 Notice of	w Summary (PTO-413) Paper No(s) of Informal Patent Application (PTO-152)		

DETAILED ACTION

Drawings

1. Figures 4A-4D should be designated by a legend such as --Prior Art-- because only that

which is old is illustrated. See MPEP § 608.02(g). A proposed drawing correction or

corrected drawings are required in reply to the Office action to avoid abandonment of the

application. The objection to the drawings will not be held in abeyance.

Claim Rejections - 35 USC § 103

1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all

obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

2. Claims 1-2 are rejected under 35 U.S.C. 103(a) as being unpatentable over the applicant's admitted prior art (AAPA) of this application in view of Nakajima et al. (U.S. Patent

6,133,150) and Muroyama (U.S. Patent 6,126,514).

AAPA teaches a method of producing a semiconductor device, comprising the

steps of (see Related Art on pages 1-3 of this application and FIGS. 4A-4D):

dry etching an upper layer pattern of an insulating film 3 in a state where at least a

part of the insulating film formed on a substrate is exposed.

AAPA fails to teach exposing a surface of the insulating film comprises silicon

oxide to a firm formation atmosphere of the insulating film as recited in present claim 1.

Nakajima teaches exposing a surface of the silicon oxide film 81 in the $N_2/H_2/H_20$

atmosphere wherein the temperature of film formation is 700 to 900°C. See col. 20, lines

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29-39 and FIG. 14D. <u>It would have been obvious to one of ordinary skill in the art</u> to incorporate Nakajima's teaching into AAPA's method because in doing so the film thickness of the insulating film can be restore. See col. 20, lines 32-36.

AAPA fails to teach the insulating film is formed by a chemical vapor deposition (CVD) method as recited in present claim 2.

Muroyama teaches that an interlayer insulating film made from silicon oxide is formed by the CVD (chemical vapor deposition) process using a source gas TEOS (tetraethoxysilane). See col. 7, lines 7-20. *It would have been obvious to one of ordinary skill in the art* to incorporate Muroyama's teaching into AAPA's method because in doing so the interlayer insulating film can be polish. See col. 7, lines 25-28.

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Khiem D Nguyen whose telephone number is (703) 306-0210. The examiner can normally be reached on Monday-Friday (8:00 AM - 5:00 PM).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Wael Fahmy can be reached on (703) 308-4918. The fax phone numbers for the organization where this application or proceeding is assigned are (703) 746-9179 for regular communications and (703) 746-9179 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

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K.N. June 6, 2002

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LONG PHANA LONG PHANA PRIMARY EXAMINER